

TOSHIBA Diode Silicon Epitaxial Planar Type

1SS362

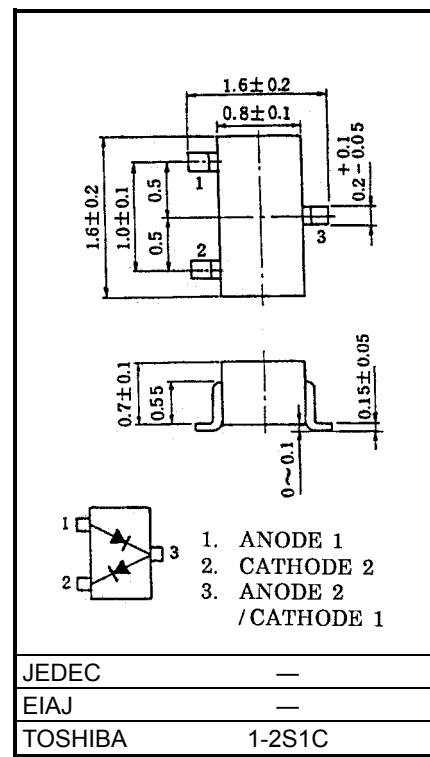
Ultra High Speed Switching Application

Unit: mm

- Small package
- Low forward voltage : $V_F = 0.97V$ (typ.)
- Fast reverse recovery time: $t_{rr} = 1.6ns$ (typ.)
- Small total capacitance : $C_T = 0.5pF$ (typ.)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	240 *	mA
Average forward current	I_O	80 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	100	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~125	°C

* Unit rating. Total rating = unit rating $\times 0.7$ 

Weight: 2.4mg

Electrical Characteristics ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V_F (1)	—	$I_F = 1mA$	—	0.63	—	V
	V_F (2)	—	$I_F = 10mA$	—	0.75	—	
	V_F (3)	—	$I_F = 100mA$	—	0.97	1.20	
Reverse current	I_R (1)	—	$V_R = 30V$	—	—	0.1	μA
	I_R (2)	—	$V_R = 80V$	—	—	0.5	
Total capacitance	C_T	—	$V_R = 0, f = 1MHz$	—	0.5	3.0	pF
Reverse recovery time	t_{rr}	—	$I_F = 10mA$, Fig.1	—	1.6	4.0	ns

Marking